



D. Thin Film Process Technology 분과

2019년 2월 15일(금), 09:00-10:45

Room F (실버홀, 5층)

[FF1-D] Device Fabrication I

좌장: 김성근 박사(KIST), 김건환 선임연구원(KRICT)

FF1-D-1 09:00-09:15	Impact of Film Thickness Control on Ferroelectric Field-Effect of Metal -Ferroelectric-Insulator-Semiconductor Capacitors Using Hf_{0.5}Zr_{0.5}O₂ Films Dae-Hong Min and Sung-Min Yoon <i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</i>
FF1-D-2 09:15-09:45	[초청] Quantum Mechanical Simulation Studies of Surface Reactions during Atomic Layer Deposition Bonggeun Shong <i>Department of Chemical Engineering, Hongik University</i>
FF1-D-3 09:45-10:00	Low Temperature NO₂ Gas Sensors based on P-type SnO Thin-Film and Thin-Film Transistors Hwan-Seok Jeong, Min-Jae Park, and Hyuck-In Kwon <i>School of Electrical and Electronics Engineering, Chung-Ang University</i>
FF1-D-4 10:00-10:15	Electronic and Physical Structures of Atomic-Layer Deposited BeO on β-Ga₂O₃ Substrates Jongho Jung ^{1,2} , Seung Min Lee ^{1,2} , Jung Hwan Yum ³ , and Jungwoo Oh ^{1,2} <i>¹School of Integrated Technology, Yonsei University, ²Yonsei Institute of Convergence Technology, Yonsei University, ³Center for Multifunctional Carbon Materials, IBS</i>
FF1-D-5 10:15-10:30	Threshold Switching and Synaptic Characteristics with Nitrogen doped Graphene Oxide Quantum Dots (N-GOQDs) Andrey S. Sokolov, Yu-Rim Jeon, Gul Hassan Rahi and Changhwan Choi <i>Division of Materials Science and Engineering, Hanyang University</i>
FF1-D-6 10:30-10:45	Flexible Charge-Trap Memory Transistors Fabricated on Ultra-Thin PI Substrates Using PEDOT:PSS Electrodes and Oxide Semiconductors Ji-Hee Yang ¹ , Do-Kyun Kim ² , Myung-Han Yoon ² , and Sung-Min Yoon ¹ <i>¹Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University, ²School of Materials Science and Engineering, GIST</i>